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UP-2814
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TECHNOLOGY CENTER 2000

10. Commissioner of Patents and Trademarks
Washington, D.C. 20231

Fr: George O. Saile, Reg. No. 19,572
20 McIntosh Drive
Poughkeepsie, N.Y. 12603

Subject:

Serial No. 09/186,388 11/05/98

B.H. Lee, Teck Hong Low, H.R. Wang,
Tang Ying, Zadig Lam

N TYPE IMPURITY DOPING USING
IMPLANTATION OF P+ IONS OR As+ IONS

Grp. Art Unit: 2814

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56. Copies of each document is included herewith.

"I hereby state that each item of information contained in
this Information Disclosure Statement was first cited in any
communication from a foreign patent office in a counterpart
foreign application not more than 3 months prior to the filing
of this statement."

U.S. Patent 4,560,879 to Wu et al., "Method and Apparatus for Implantation of Doubly-Charged Ions", discloses an ion implantation apparatus and method for reducing contamination of doubly-charged ions by singly-charged ions.

S. Wolf et al., "Silicon Processing for the VLSI Era, Volume 2: Process Integration", Lattice Press, Sunset Beach, California, copyright 1990, pp. 332-334, discusses having source/drain regions or a polysilicon electrode as the semiconductor wafer.

Sincerely,

A handwritten signature in cursive script that reads "George O. Saile".

George O. Saile,
Reg. No. 19572